

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph 28 with the following paragraph.

[0028] Another embodiment shown in FIG. 4 forms separated wells, a first well ~~400~~ 410 for the photoreceptor 405 and a second well 430 for the readout circuit 435. This device is shown in charge integration mode, having lower positions corresponding to lower voltages. Holes may be integrated under the photogate 405 to form charge which is stored in one of the bridge diffusions 412 within the photo gate. The photogate is located in the first well 410. In this embodiment, the photogate may be reset within the first N well 410. The photogate is reset by activating the gate 408 to bring the photogate level to the reset level V_{rst} . This has the effect of clearing the charge within the photogate 405 as well as the bridge diffusions 412 and 414. An anti blooming gate 413 may also be located within the first well 410.